

### **Features**

- 40V/38A,  $R_{DS(ON)} = 13m\Omega \text{ (Max.)} @ V_{G\overline{S}} = 10V$  $R_{DS(ON)} = 16m\Omega \text{ (Max.)} @ V_{GS} = 4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

## **Applications**

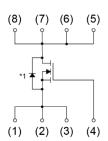
 Power Management in Desktop Computer or DC/DC Converters.

## **Pin Description**



DFN3.3X3.3\_EP





N-Channel MOSFET

### **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit					
Common Ratings								
$V_{DSS}$	Drain-Source Voltage	40	_ v					
$V_{GSS}$	Gate-Source Voltage	±20						
TJ	Maximum Junction Temperature	150	- °C					
T <sub>STG</sub>	Storage Temperature Range	-55 to 150						
Is	Diode Continuous Forward Current	T <sub>A</sub> =25°C	2	Α				
	Continuous Drain Current	T <sub>c</sub> =25°C	38					
l <sub>D</sub>		T <sub>c</sub> =70°C	20	Α				
I <sub>DM</sub> <sup>a</sup>	Pulsed Drain Current	T <sub>A</sub> =25°C	36	$\neg$				
P <sub>D</sub>	Maximum Power Dissipation	T <sub>A</sub> =25°C	2.1	W				
		T <sub>A</sub> =70°C	1.5					
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	t ≤ 10s	30					
		Steady State	60	°C/W				
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	20					
I <sub>AS</sub> b	Avalanche Current, Single pulse	L=0.1mH	23	Α				
E <sub>AS</sub> <sup>b</sup>	Avalanche Energy, Single pulse	L=0.1mH	26	mJ				

Note a: Max. current is limited by bonding wire.

Note b: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T<sub>i</sub>=25°C).



# **Electrical Characteristics** (T<sub>A</sub> = 25°C Unless Otherwise Noted)

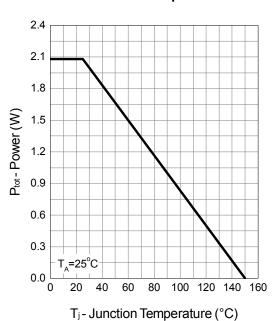
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit		
Static Characteristics									
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250μA		40	-	-	V		
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V		-	-	1			
			T <sub>J</sub> =85°C	-	-	30	μА		
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 2$	50μΑ	1.5	1.8	2.5	V		
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V		-	-	±100	nA		
	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =7A		-	10.5	13			
R <sub>DS(ON)</sub> c			T <sub>J</sub> =125°C	-	15.75	-	mΩ		
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =	5A	-	- 12 16				
Gfs	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>DS</sub> =15A		-	31	-	S		
Diode Ch	aracteristics	·							
V <sub>SD</sub> <sup>c</sup>	Diode Forward Voltage	I <sub>SD</sub> =10A, V <sub>GS</sub> =0	V	-	0.9	1.1	V		
t <sub>rr</sub>	Reverse Recovery Time			-	15.2	-			
t <sub>a</sub>	Charge Time	$V_{DD}$ =20V, $I_{SD}$ =10A, $dI_{SD}/dt$ =100A/ $\mu$ s		-	9.4	-	ns		
t <sub>b</sub>	Discharge Time			-	5.8	-			
Q <sub>rr</sub>	Reverse Recovery Charge			-	9.5	-	nC		
Dynamic	Characteristics <sup>d</sup>								
$R_{G}$	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0\	/,F=1MHz	0.7	1.1	1.8	Ω		
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,			1125	-	pF		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =20V, Frequency=1.0MHz		-	132	-			
C <sub>rss</sub>	Reverse Transfer Capacitance			-	70	-			
t <sub>d(ON)</sub>	Turn-on Delay Time				12.6	-			
t <sub>r</sub>	Turn-on Rise Time	$V_{DD}$ =20V, R <sub>L</sub> =2 $I_{DS}$ =1A, $V_{GEN}$ =1		-	10	-			
t <sub>d(OFF)</sub>	Turn-off Delay Time	$R_{G}=1\Omega$		-	23.6	-	ns		
t <sub>f</sub>	Turn-off Fall Time			-	6	-			
Gate Charge Characteristics <sup>d</sup>									
Qg	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> = I <sub>DS</sub> =7A	4.5V,	-	9.4	-			
$Q_g$	Total Gate Charge	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>DS</sub> =7A		-	20	28			
$Q_{gth}$	Threshold Gate Charge			-	2	-	nC		
$Q_{gs}$	Gate-Source Charge			-	3.9	-			
$Q_{gd}$	Gate-Drain Charge			-	3	-			

Note c : Pulse test ; pulse width≤300μs, duty cycle≤2%.

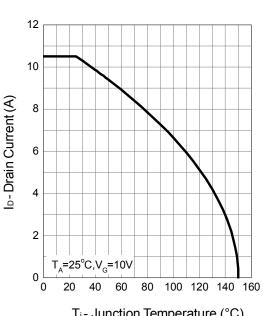


### **Typical Operating Characteristics**

# **Power Dissipation**

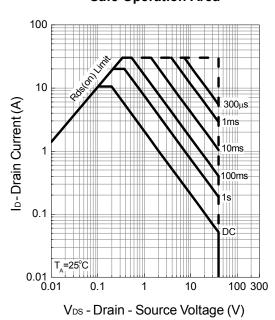


#### **Drain Current**

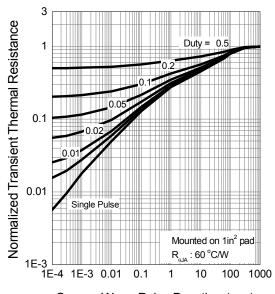


T<sub>j</sub>- Junction Temperature (°C)

#### Safe Operation Area



#### **Thermal Transient Impedance**

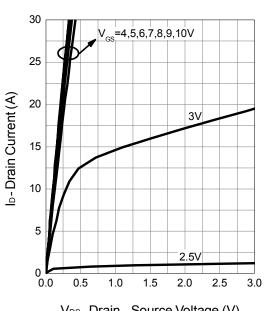


Square Wave Pulse Duration (sec)



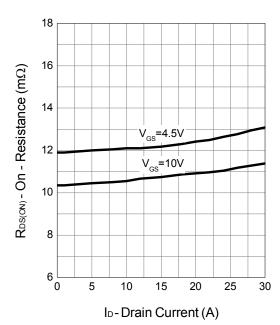
# **Typical Operating Characteristics (Cont.)**

# **Output Characteristics**

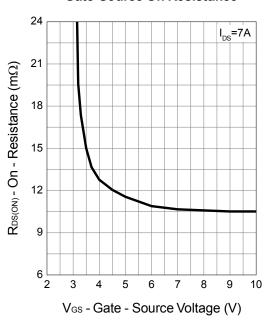


V<sub>DS</sub> - Drain - Source Voltage (V)

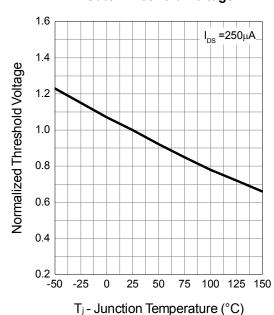
#### **Drain-Source On Resistance**



#### **Gate-Source On Resistance**



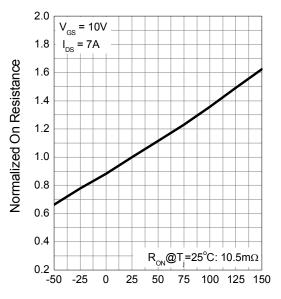
#### **Gate Threshold Voltage**





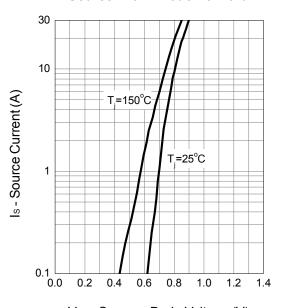
# **Typical Operating Characteristics (Cont.)**

### **Drain-Source On Resistance**



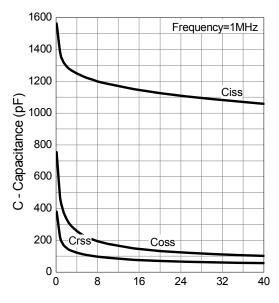
T<sub>j</sub> - Junction Temperature (°C)

#### Source-Drain Diode Forward



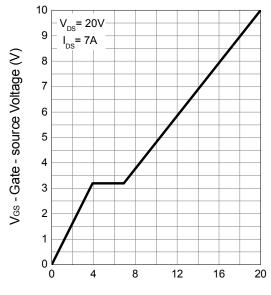
VsD - Source - Drain Voltage (V)

#### Capacitance



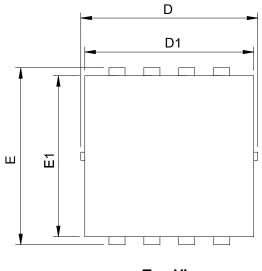
V<sub>DS</sub> - Drain - Source Voltage (V)

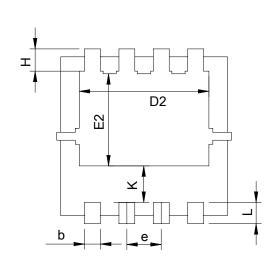
#### **Gate Charge**



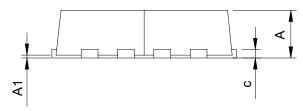
Q<sub>G</sub> - Gate Charge (nC)







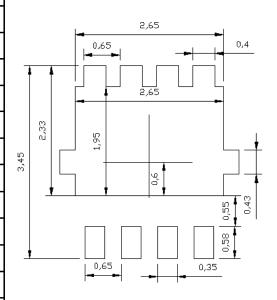
**Top View** 



**Bottom View** 

#### **Side View**

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<i>∾</i> ≻≦⊞О∟	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
Α	0.70	1.00	0.028	0.039	
A1	0.00	0.05	0.000	0.002	
b	0.25	0.35	0.010	0.014	
С	0.14	0.20	0.006	0.008	
D	3.10	3.50	0.122	0.138	
D1	3.05	3.25	0.120	0.128	
D2	2.35	2.55	0.093	0.100	
Е	3.10	3.50	0.122	0.138	
E1	2.90	3.10	0.114	0.122	
E2	1.64	1.84	0.065	0.072	
е	0.65 BSC		0.026 BSC		
Н	0.32	0.52	0.013	0.020	
К	0.59	0.79	0.023	0.031	
L	0.25	0.55	0.010	0.022	



**UNIT:** mm



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